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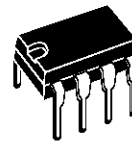
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1.2W AUDIO AMPLIFIER

DESCRIPTION

The TBA820M is a monolithic integrated audio amplifier in a 8 lead dual in-line plastic package. It is intended for use as low frequency class B power amplifier with wide range of supply voltage: 3 to 16V, in portable radios, cassette recorders and players etc. Main features are: minimum working supply voltage of 3V, low quiescent current, low number of external components, good ripple rejection, no cross-over distortion, low power dissipation.

Output power: $P_o = 2W$ at $12V/8\Omega$, $1.6W$ at $9V/4\Omega$ and $1.2W$ at $9V/8\Omega$.



Minidip

ORDERING NUMBER: TBA820M

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_s	Supply voltage	16	V
I_o	Output peak current	1.5	A
P_{tot}	Power dissipation at $T_{amb} = 50^\circ C$	1	W
T_{stg}, T_j	Storage and junction temperature	-40 to 150	$^\circ C$

TEST AND APPLICATION CIRCUITS

Figure 1. Circuit diagram with load connected to the supply voltage

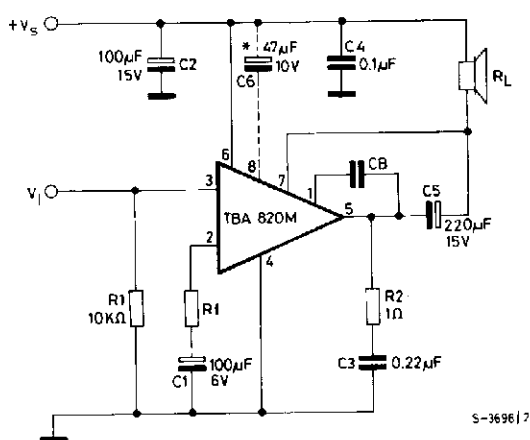
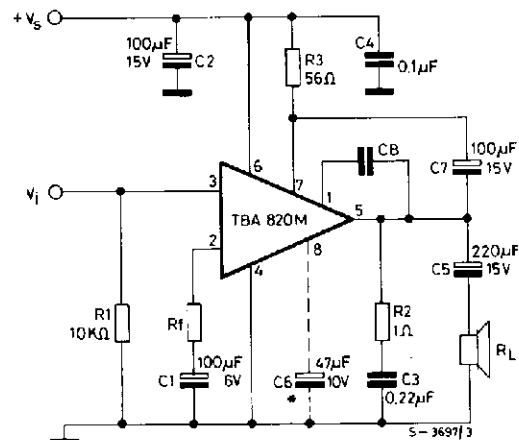


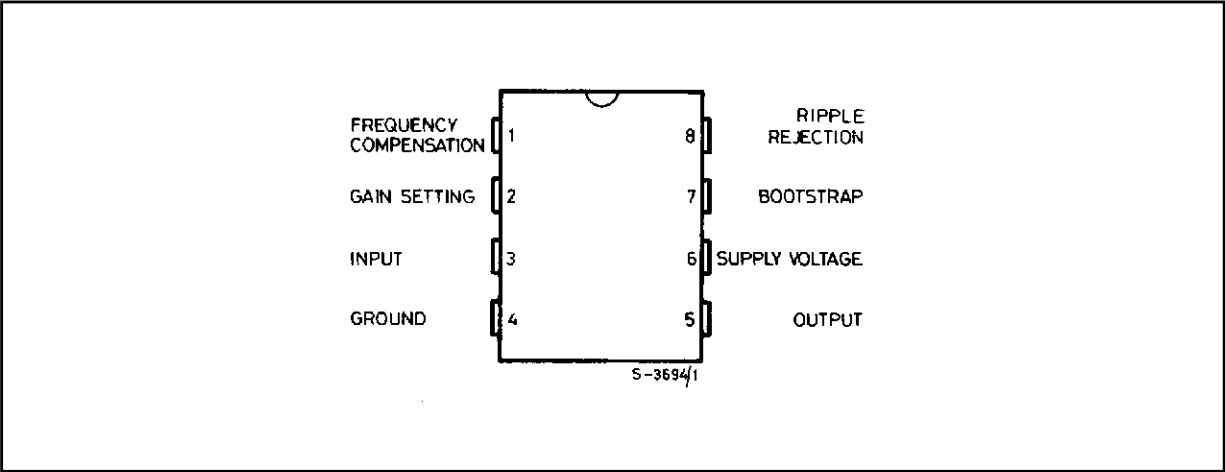
Figure 2. Circuit diagram with load connected to ground



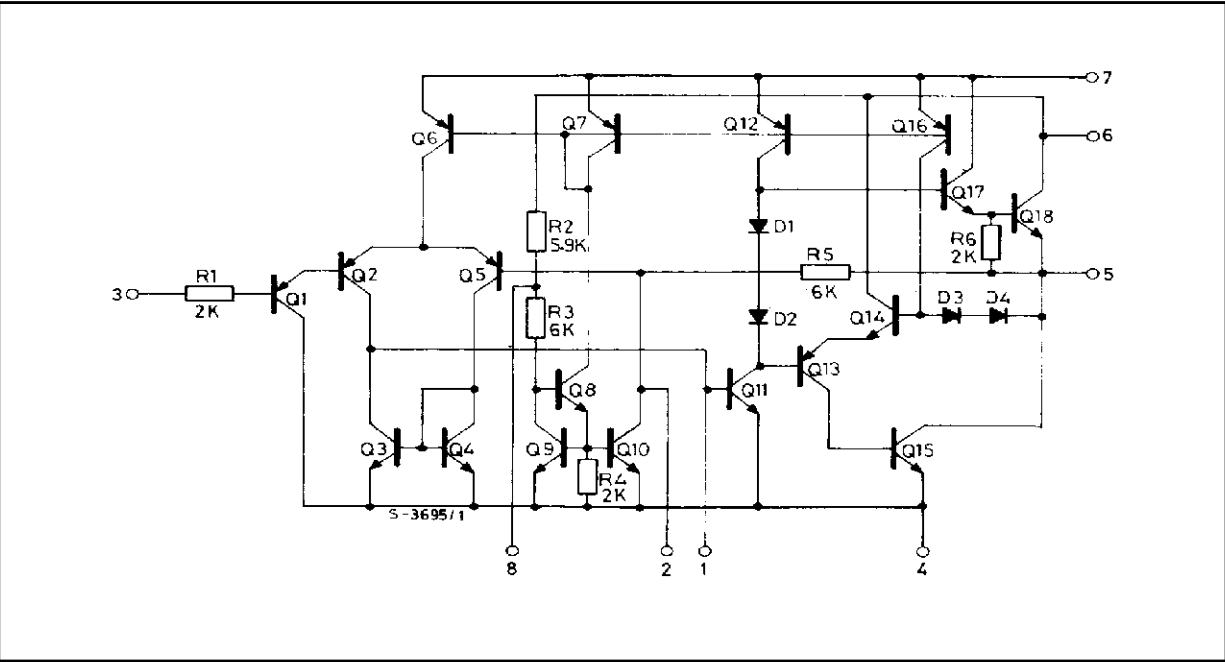
* Capacitor C6 must be used when high ripple rejection is requested.

TBA820M

PIN CONNECTION (top view)



SCHEMATIC DIAGRAM



THERMAL DATA

Symbol	Parameter	Value	Unit
$R_{th-j-amb}$	Thermal resistance junction-ambient	max 100	°C/W

ELECTRICAL CHARACTERISTICS (Refer to the test circuits $V_s = 9V$, $T_{amb} = 25\text{ }^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test conditions		Min.	Typ.	Max.	Unit
V _s	Supply voltage			3		16	V
V _o	Quiescent output voltage (pin 5)			4	4.5	5	V
I _d	Quiescent drain current				4	12	mA
I _b	Bias current (pin 3)				0.1		μA
P _o	Output power	d = 10% R _f = 120Ω V _s = 12V V _s = 9V V _s = 9V V _s = 6V V _s = 3.5V	f = 1 kHz R _L = 8Ω R _L = 4Ω R _L = 8Ω R _L = 4Ω R _L = 4Ω	0.9	2 1.6 1.2 0.75 0.25		W W W W W
R _i	Input resistance (pin 3)	f = 1 kHz			5		MΩ
B	Frequency response (-3 dB)	R _L = 8Ω C ₅ = 1000 μF R _f = 120Ω	C _B = 680 pF	25 to 7,000			Hz
			C _B = 220 pF	25 to 20,000			
d	Distortion	P _o = 500 mW R _L = 8Ω f = 1 kHz	R _f = 33Ω		0.8		%
			R _f = 120Ω		0.4		
G _v	Voltage gain (open loop)	f = 1 kHz R _L = 8Ω			75		dB
G _v	Voltage gain (closed loop)	R _L = 8Ω	R _f = 33Ω		45		dB
		f = 1 kHz	R _f = 120Ω		34		
e _N	Input noise voltage (*)				3		μV
i _N	Input noise current (*)				0.4		nA
$\frac{S+N}{N}$	Signal to noise ratio (*)	P _o = 1.2W R _L = 8Ω G _v = 34 dB	R1 = 10KΩ		80		dB
			R1 = 50 kΩ		70		
SVR	Supply voltage rejection (test circuit of fig. 2)	R _L = 8Ω f _(ripple) = 100 Hz C6 = 47 μF R _f = 120Ω			42		dB

(*) B = 22 Hz to 22 KHz

Figure 3. Output power vs. supply voltage

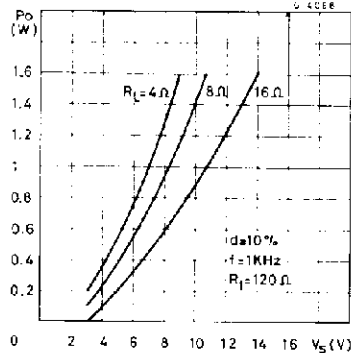


Figure 4. Harmonic distortion vs. output power

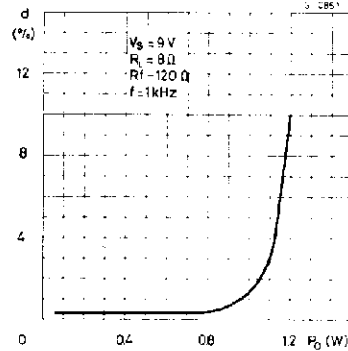


Figure 5. Power dissipation and efficiency vs. output power

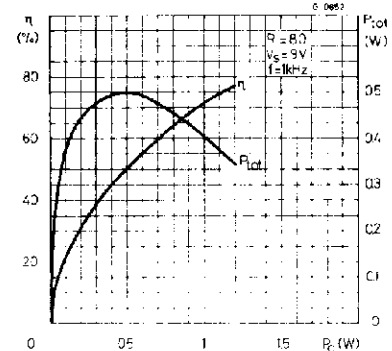


Figure 6. Maximum power dissipation (sine wave operation)

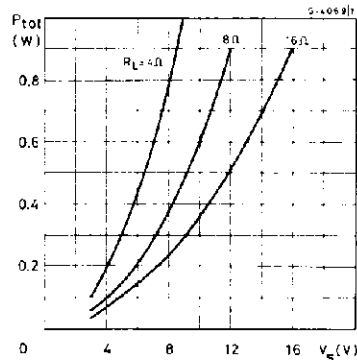


Figure 7. Suggested value of CB vs. Rf

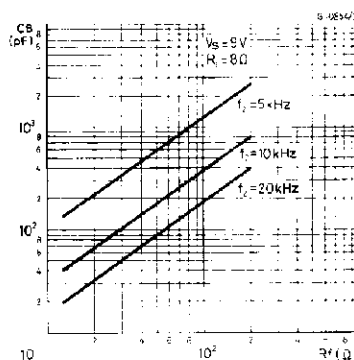


Figure 8. Frequency response

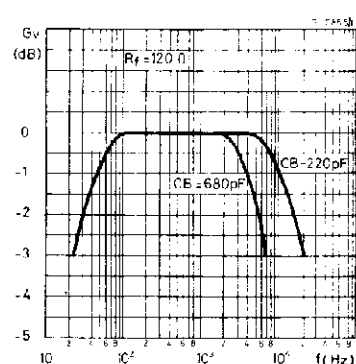


Figure 9. Harmonic distortion vs. frequency

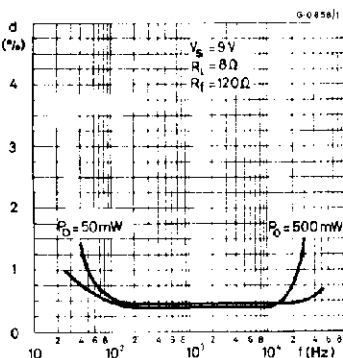


Figure 10. Supply voltage rejection (Fig. 2 circuit)

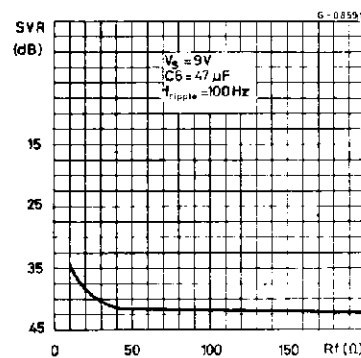
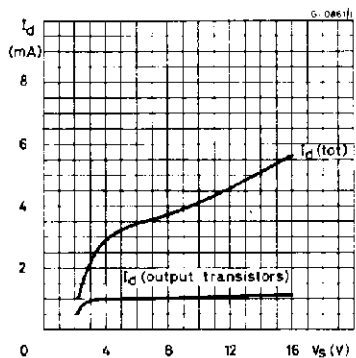
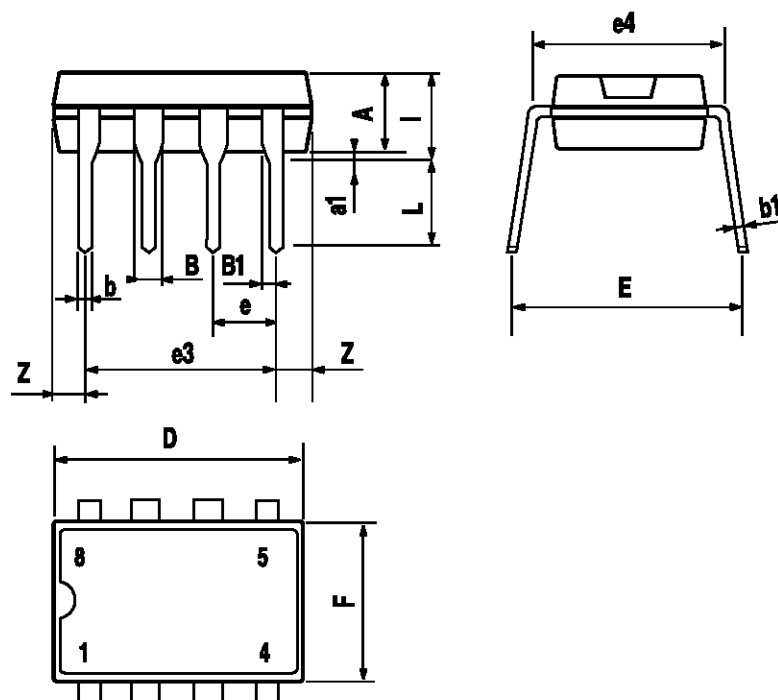


Figure 11. Quiescent current vs. supply voltage



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DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A		3.32			0.131	
a1	0.51			0.020		
B	1.15		1.65	0.045		0.065
b	0.356		0.55	0.014		0.022
b1	0.204		0.304	0.008		0.012
D			10.92			0.430
E	7.95		9.75	0.313		0.384
e		2.54			0.100	
e3		7.62			0.300	
e4		7.62			0.300	
F			6.6			0.260
I			5.08			0.200
L	3.18		3.81	0.125		0.150
Z			1.52			0.060



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